

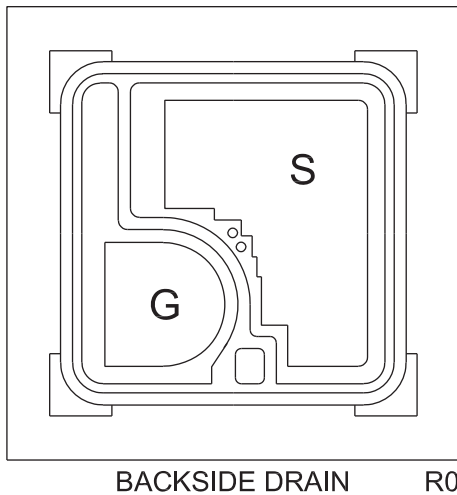
**PROCESS CP359R**  
**Small Signal MOSFET**  
N-Channel Enhancement-Mode MOSFET Chip



**PROCESS DETAILS**

Die Size	9.1 x 9.1 MILS
Die Thickness	3.9 MILS
Gate Bonding Pad Area	2.5 MILS DIAMETER
Source Bonding Pad Area	3.9 x 3.9 MILS
Top Side Metalization	Al-Si - 30,000Å
Back Side Metalization	Au - 12,000Å

**GEOMETRY**



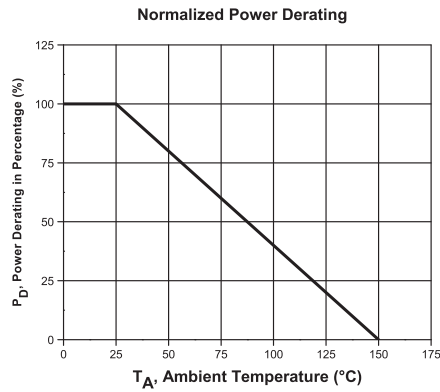
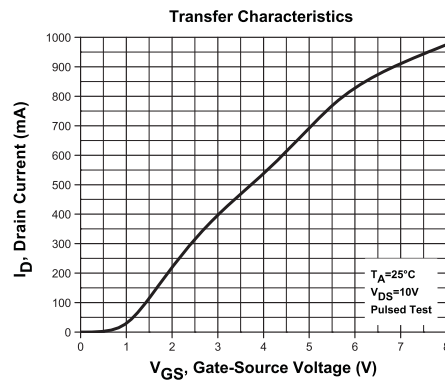
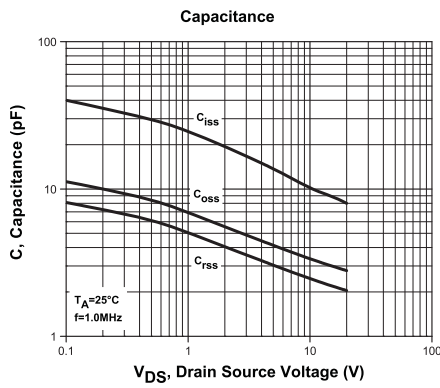
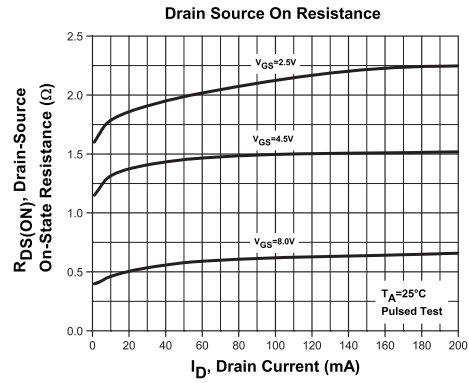
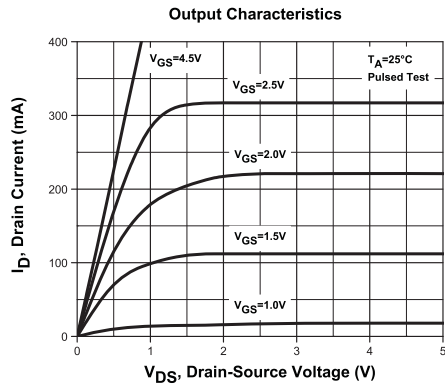
**GROSS DIE PER 6 INCH WAFER**  
290,000

**PRINCIPAL DEVICE TYPE**  
CMRDM3590

R0 (13-May 2010)

# PROCESS CP359R

## Typical Electrical Characteristics



R0 (13-May 2010)